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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10066627	FILING DATE 02/06/2002	CLASS 438	SUBCLASS 791	GAU 2812	EXAMINER GUERRA
**APPLICANTS: Kato Hitoshi; Fukushima Kohei; Endo Atsushi; Nishita Tatsuo; Kumagai Takeshi;					
**CONTINUING DATA VERIFIED:					
**FOREIGN APPLICATIONS VERIFIED: JAPAN 2001-030544 02/07/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO 33082M119	
Verified and Acknowledged Examiners's initials <i>MC</i>					
TITLE : Silicon nitride film forming method, silicon nitride film forming system and silicon nitride film forming system precleaning method					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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